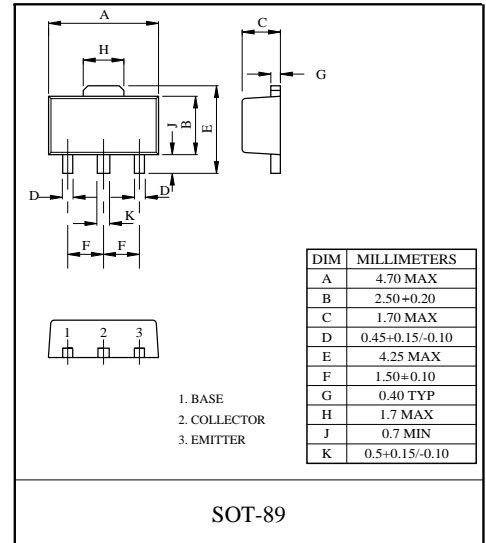


FTC4379 TRANSISTOR (NPN)

FEATURES

- Complementary to FTA1666
- Small Flat Package
- Low Saturation Voltage
- Power Amplifier and Switching Application



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	50	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	2	A
P _C	Collector Power Dissipation	500	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	250	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

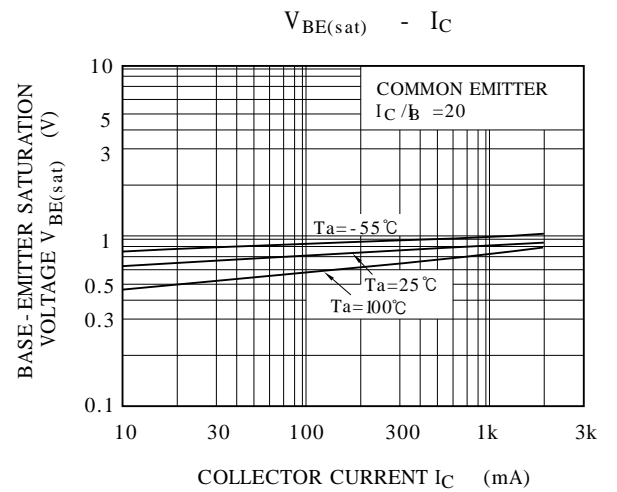
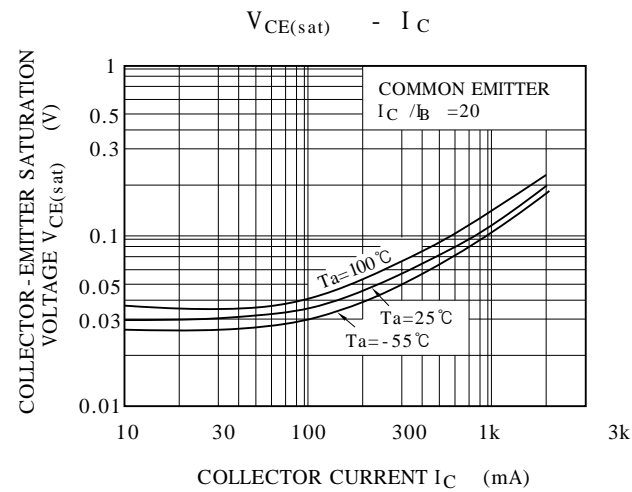
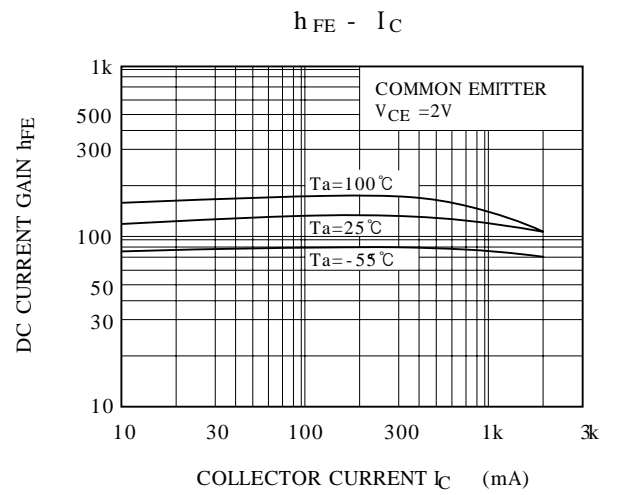
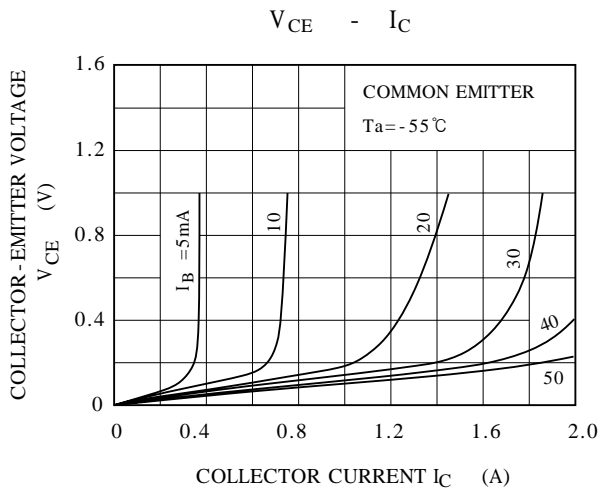
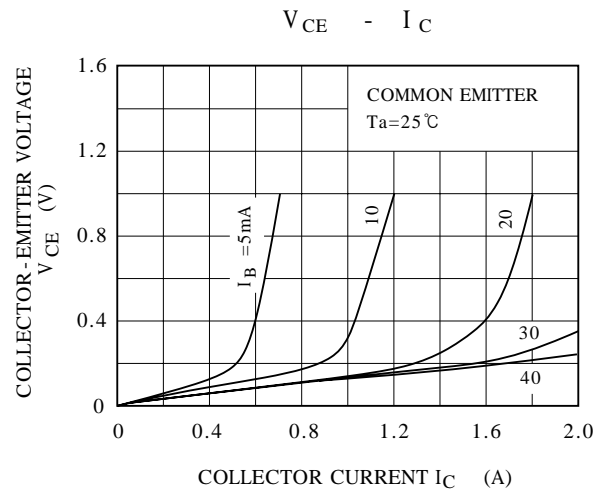
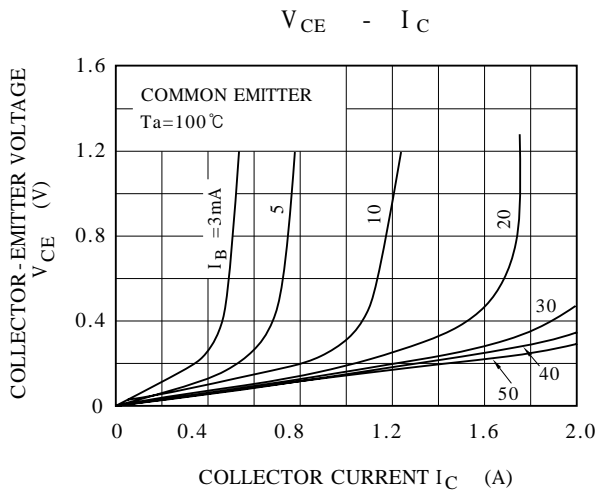
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 1mA, I _E =0	50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 1mA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =50V, I _E =0			100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			100	nA
DC current gain	h _{FE(1)} *	V _{CE} =2V, I _C = 500mA	70		240	
	h _{FE(2)} *	V _{CE} =2V, I _C = 1.5A	40			
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C = 1A, I _B = 50mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C = 1A, I _B = 50mA			1.2	V
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			40	pF
Transition frequency	f _T	V _{CE} = 2V, I _C = 500mA		120		MHz
Switching Time	Turn on time	t _{on}		0.1		uS
	Storage time	t _{stg}		1.0		
	Fall time	t _f		0.1		

*Pulse test: pulse width ≤300mS, duty cycles ≤ 2.0%.

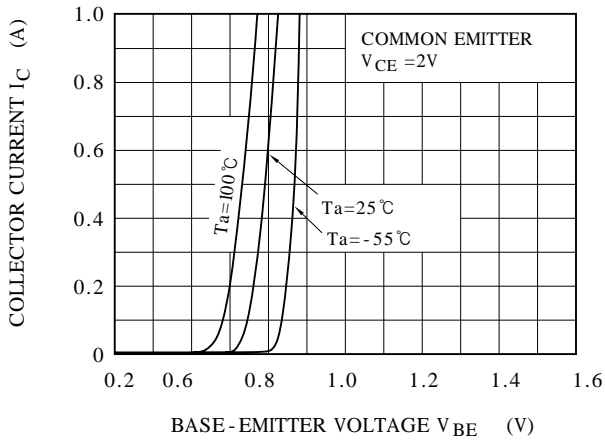
CLASSIFICATION OF h_{FE(1)}

RANK	O	Y
RANGE	70 - 140	120 - 240
MARKING	UO	UY

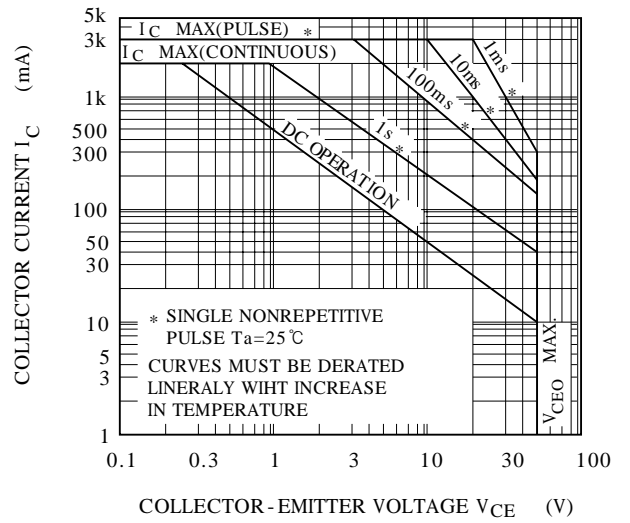
FTC4379



$I_C - V_{BE}$



SAFE OPERATING AREA



$P_C - T_a$

